



THE DATASHEET OF BSS138LT1G



MOSFET – Power, N-Channel, SOT-23 200 mA, 50 V

BSS138L, BVSS138L

Typical applications are DC–DC converters, power management in portable and battery–powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

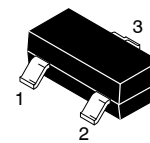
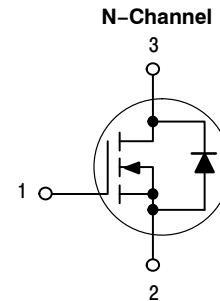
- Low Threshold Voltage ($V_{GS(th)}$: 0.85 V–1.5 V) Makes it Ideal for Low Voltage Applications
- Miniature SOT–23 Surface Mount Package Saves Board Space
- HBM Class 0A, MM Class M1A, CDM Class IV (Note 3)
- BVSS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|-----------------|-------------|---------------------------|
| Drain–to–Source Voltage | V_{DSS} | 50 | Vdc |
| Gate–to–Source Voltage – Continuous | V_{GS} | ± 20 | Vdc |
| Drain Current | | | mA |
| – Continuous @ $T_A = 25^\circ\text{C}$ | I_D | 200 | |
| – Pulsed Drain Current ($t_p \leq 10 \mu\text{s}$) | I_{DM} | 800 | |
| Total Power Dissipation @ $T_A = 25^\circ\text{C}$ | P_D | 225 | mW |
| Operating and Storage Temperature Range | T_J, T_{stg} | – 55 to 150 | $^\circ\text{C}$ |
| Thermal Resistance, Junction–to–Ambient | $R_{\theta JA}$ | 556 | $^\circ\text{C}/\text{W}$ |
| Maximum Lead Temperature for Soldering Purposes, for 10 seconds | T_L | 260 | $^\circ\text{C}$ |

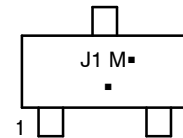
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

200 mA, 50 V
 $R_{DS(on)} = 3.5 \Omega$



SOT-23
CASE 318
STYLE 21

MARKING DIAGRAM



J1 = Device Code
M = Date Code*
▪ = Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping† |
|----------------------------|---------------------|----------------------|
| BSS138LT1G, BVSS138LT1G | SOT-23 (Pb–Free) | 3,000 / Tape & Reel |
| BSS138LT7G | SOT-23 (Pb–Free) | 3,500 / Tape & Reel |
| BSS138LT3G, BVSS138LT3G | SOT-23 (Pb–Free) | 10,000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BSS138L, BVSS138L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | |
|---|----------------------|----|---|-------------------|------|
| Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 250 μAdc) | V _{(BR)DSS} | 50 | – | – | Vdc |
| Zero Gate Voltage Drain Current (V _{DS} = 25 Vdc, V _{GS} = 0 Vdc, 25°C) (V _{DS} = 50 Vdc, V _{GS} = 0 Vdc, 25°C) (V _{DS} = 50 Vdc, V _{GS} = 0 Vdc, 150°C) | I _{DSS} | – | – | 0.1 0.5 5.0 | μAdc |
| Gate-Source Leakage Current (V _{GS} = ± 20 Vdc, V _{DS} = 0 Vdc) | I _{GSS} | – | – | ±0.1 | μAdc |

ON CHARACTERISTICS (Note 1)

| | | | | | |
|--|---------------------|------|-----|-----------|-------|
| Gate-Source Threshold Voltage (V _{DS} = V _{GS} , I _D = 1.0 mAdc) | V _{GS(th)} | 0.85 | – | 1.5 | Vdc |
| Static Drain-to-Source On-Resistance (V _{GS} = 2.75 Vdc, I _D < 200 mAdc, T _A = –40°C to +85°C) (V _{GS} = 5.0 Vdc, I _D = 200 mAdc) | r _{DS(on)} | – | 5.6 | 10 3.5 | Ω |
| Forward Transconductance (V _{DS} = 25 Vdc, I _D = 200 mAdc, f = 1.0 kHz) | g _{fs} | 100 | – | – | mmhos |

DYNAMIC CHARACTERISTICS

| | | | | | | |
|----------------------|--|------------------|---|-----|-----|----|
| Input Capacitance | (V _{DS} = 25 Vdc, V _{GS} = 0, f = 1 MHz) | C _{iss} | – | 40 | 50 | pF |
| Output Capacitance | (V _{DS} = 25 Vdc, V _{GS} = 0, f = 1 MHz) | C _{oss} | – | 12 | 25 | |
| Transfer Capacitance | (V _{DG} = 25 Vdc, V _{GS} = 0, f = 1 MHz) | C _{rss} | – | 3.5 | 5.0 | |

SWITCHING CHARACTERISTICS (Note 2)

| | | | | | | |
|---------------------|---|---------------------|---|---|----|----|
| Turn-On Delay Time | (V _{DD} = 30 Vdc, I _D = 0.2 Adc,) | t _{d(on)} | – | – | 20 | ns |
| Turn-Off Delay Time | | t _{d(off)} | – | – | 20 | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperature.
3. ESD between the gate and source serves only, no gate overvoltage rating is implied.

TYPICAL ELECTRICAL CHARACTERISTICS

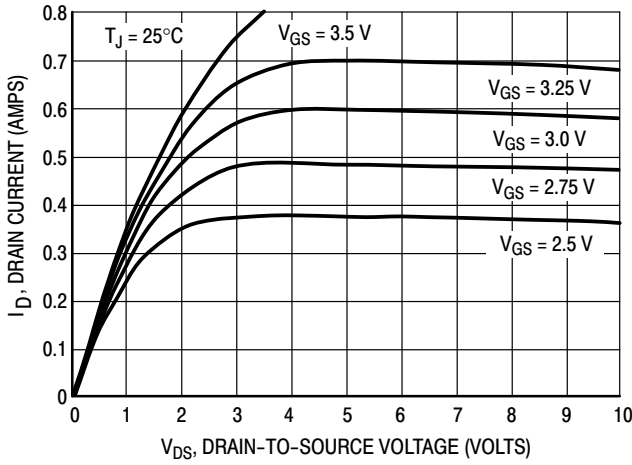


Figure 1. On-Region Characteristics

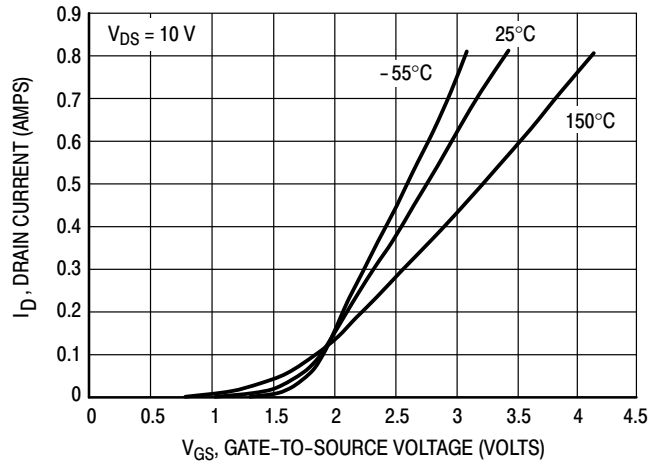


Figure 2. Transfer Characteristics

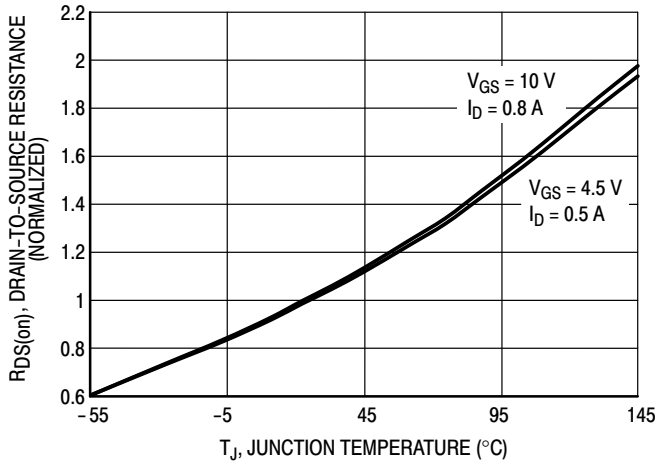


Figure 3. On-Resistance Variation with Temperature

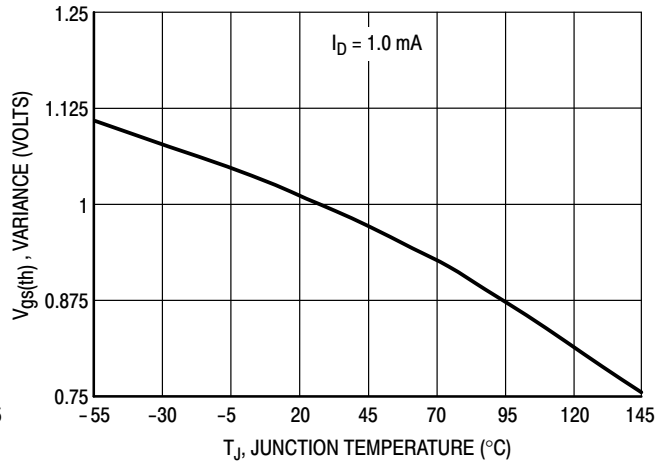


Figure 4. Threshold Voltage Variation with Temperature

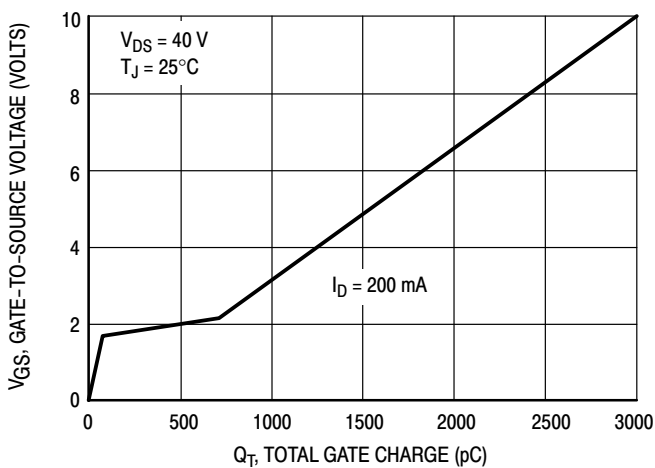


Figure 5. Gate Charge

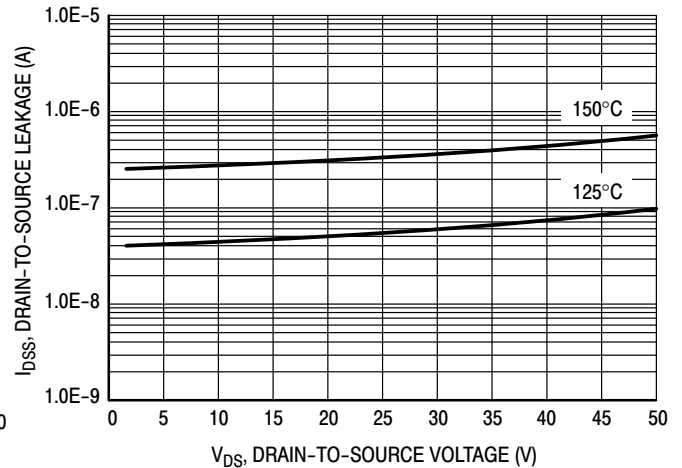


Figure 6. IDSS

BSS138L, BVSS138L

TYPICAL ELECTRICAL CHARACTERISTICS

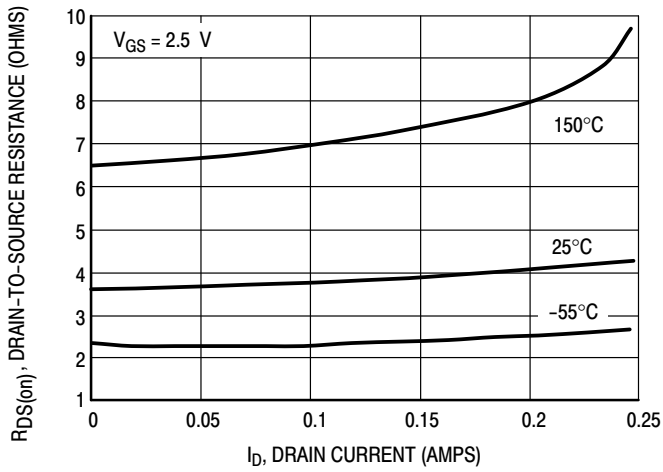


Figure 7. On-Resistance versus Drain Current

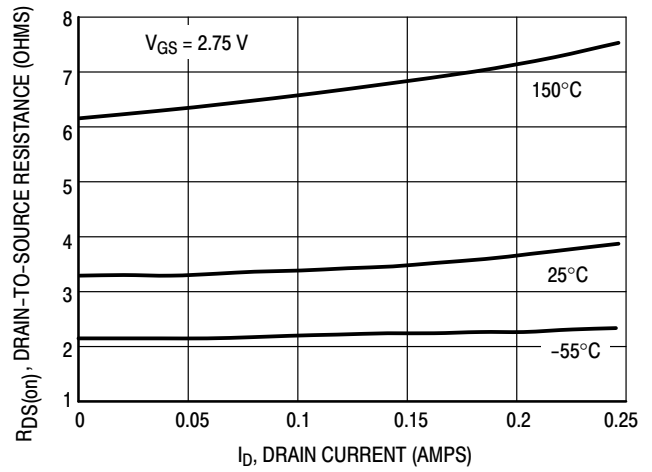


Figure 8. On-Resistance versus Drain Current

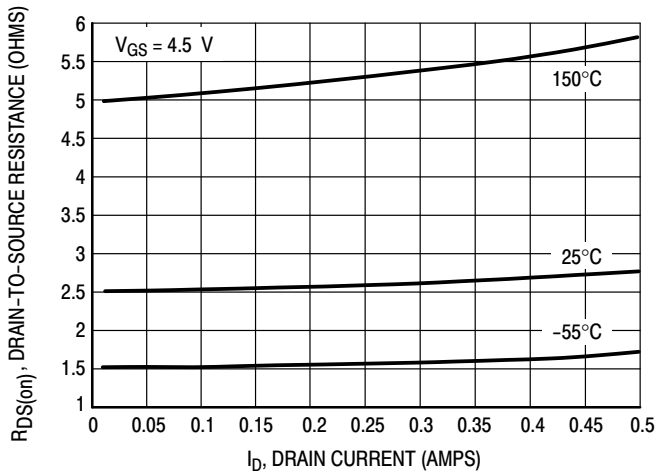


Figure 9. On-Resistance versus Drain Current

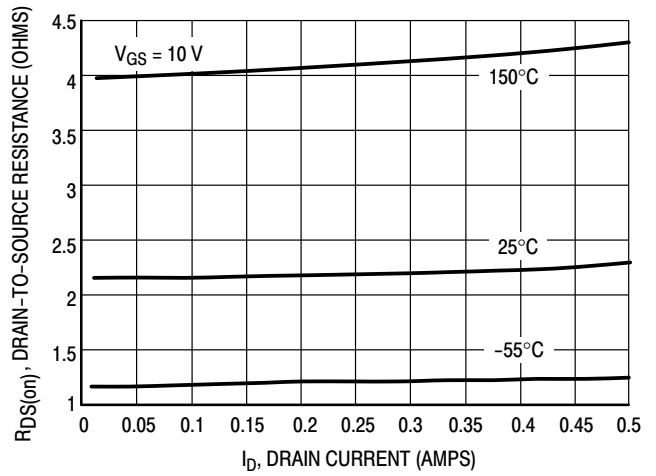


Figure 10. On-Resistance versus Drain Current

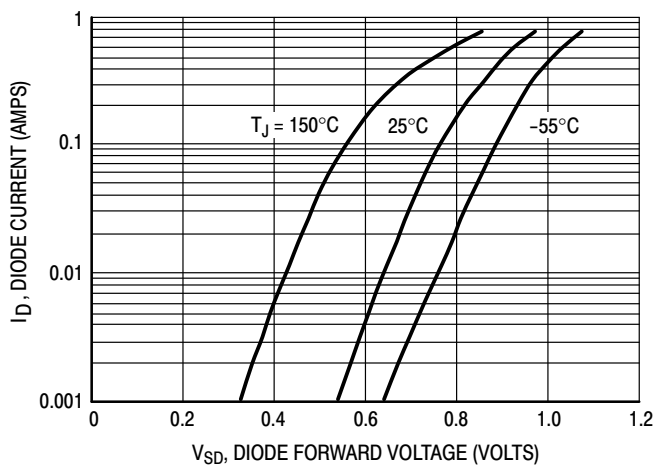


Figure 11. Body Diode Forward Voltage

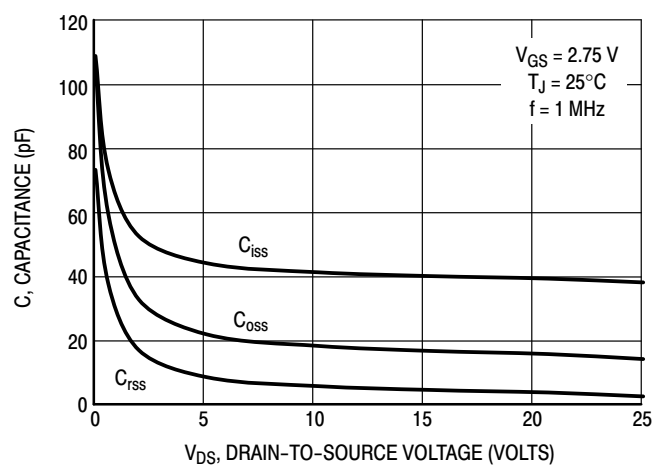


Figure 12. Capacitance

BSS138L, BVSS138L

TYPICAL ELECTRICAL CHARACTERISTICS

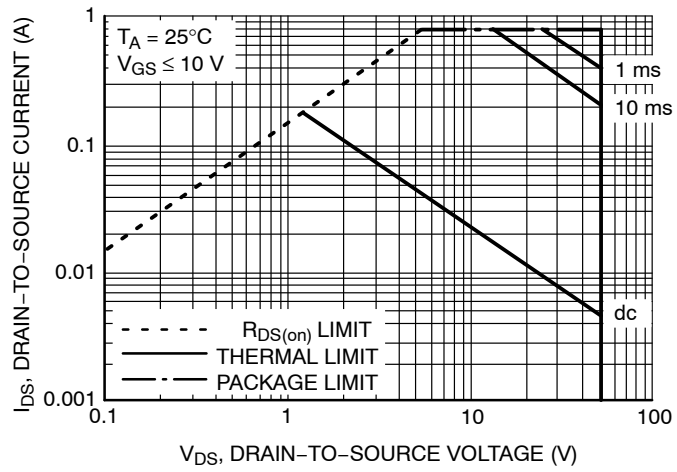


Figure 13. Safe Operating Area

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| DIM | MILLIMETERS | | | INCHES | | |
|----------------|-------------|------|------|--------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| c | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| H _E | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| T | 0° | --- | 10° | 0° | --- | 10° |

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
 M = Date Code
 ▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

| | | |
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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

| | | | | | |
|---|---|---|---|---|---|
| STYLE 1 THRU 5: CANCELLED | STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE | | |
| STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE | STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE | STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE | STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE | STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE |
| STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE | STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE | STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE | STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE | STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE | STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE |
| STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN | STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT | STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE | STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE | STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE | STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION |
| STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE | STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE | | | | |

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